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Switch-mode Power Rectifiers

DPAK Surface Mount Package

MBRD320G, MBRD330G, MBRD340G, MBRD350G, MBRD360G

These state−of−the−art devices are designed for use as output rectifiers, free wheeling, protection and steering diodes in switching power supplies, inverters and other inductive switching circuits.

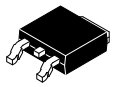
Features

- Extremely Fast Switching
- Extremely Low Forward Drop
- Platinum Barrier with Avalanche Guardrings
- NRVBD and SBRD Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

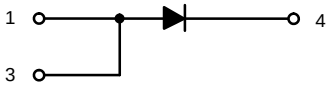
Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 0.4 Gram (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes; 260°C Max. for 10 Seconds
- ESD Ratings:
  - Machine Model = C
  - Human Body Model = 3B

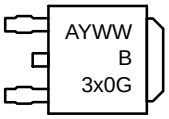
SCHOTTKY BARRIER RECTIFIERS 3.0 AMPERES, 20 − 60 VOLTS



DPAK
CASE 369C



MARKING DIAGRAM



A	= Assembly Location*
Y	= Year
WW	= Work Week
B3x0	= Device Code
x	= 2, 3, 4, 5, or 6
G	= Pb−Free Package

* The Assembly Location Code (A) is front side optional. In cases where the Assembly Location is stamped in the package bottom (molding ejecter pin), the front side assembly code may be blank.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 3.

MAXIMUM RATINGS

Rating	Symbol	MBRD/SBRD8					Unit
		320	330	340	350	360	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	30	40	50	60	V
Average Rectified Forward Current (T_C = +125°C)	$I_{F(AV)}$	3					A
Peak Repetitive Forward Current, T_C = +125°C (Square Wave, Duty = 0.5)	I_{FRM}	6					A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	75					A
Peak Repetitive Reverse Surge Current (2 μs, 1 kHz)	I_{RRM}	1					A
Operating Junction Temperature Range (Note 1)	T_J	−65 to +175					°C
Storage Temperature Range	T_{stg}	−65 to +175					°C
Voltage Rate of Change (Rated V_R)	dv/dt	10,000					V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction−to−Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	6	°C/W
Maximum Thermal Resistance, Junction−to−Ambient (Note 2)	$R_{\theta JA}$	80	°C/W

2. Rating applies when surface mounted on the minimum pad size recommended.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 3) i_F = 3 Amps, T_C = +25°C i_F = 3 Amps, T_C = +125°C i_F = 6 Amps, T_C = +25°C i_F = 6 Amps, T_C = +125°C	V_F	 0.6 0.45 0.7 0.625	V
Maximum Instantaneous Reverse Current (Note 3) (Rated dc Voltage, T_C = +25°C) (Rated dc Voltage, T_C = +125°C)	i_R	 0.2 20	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

ORDERING INFORMATION

Device	Package	Shipping†
MBRD340T4G	DPAK (Pb−Free)	2,500 Tape & Reel
SBRD8340T4G−VF01*		2,500 Tape & Reel
MBRD350T4G		2,500 Tape & Reel
MBRD360T4G		2,500 Tape & Reel
NRVBD360VT4G*		2,500 Tape & Reel

DISCONTINUED (Note 4)

MBRD320G	DPAK (Pb−Free)	75 Units / Rail
SBRD8320G*		75 Units / Rail
SBRD8320G−VF01*		75 Units / Rail
MBRD320RLG		1,800 Tape & Reel
MBRD320T4G		2,500 Tape & Reel
SBRD8320T4G*		2,500 Tape & Reel
SBRD8320T4G−VF01*		2,500 Tape & Reel
MBRD330G		75 Units / Rail
SBRD8330G*		75 Units / Rail
SBRD8330G−VF01*		75 Units / Rail
MBRD330RLG		1,800 Tape & Reel
MBRD330T4G		2,500 Tape & Reel
SBRD8330T4G*		2,500 Tape & Reel
SBRD8330T4G−VF01*		2,500 Tape & Reel
MBRD340G		75 Units / Rail
SBRD8340G*		75 Units / Rail
SBRD8340G−VF01*		75 Units / Rail
MBRD340RLG		1,800 Tape & Reel
SBRD8340T4G*		2,500 Tape & Reel
MBRD350G		75 Units / Rail
SBRD8350G*		75 Units / Rail
SBRD8350G−VF01*		75 Units / Rail
MBRD350RLG		1,800 Tape & Reel
SBRD8350RLG*		1,800 Tape & Reel
SBRD8350RLG−VF01*		1,800 Tape & Reel
SBRD8350T4G*		2,500 Tape & Reel
SBRD8350T4G−VF01*		2,500 Tape & Reel
MBRD360G		75 Units / Rail
SBRD8360G*		75 Units / Rail
SBRD8360G−VF01*		75 Units / Rail
MBRD360RLG		1,800 Tape & Reel
SBRD8360RLG*		1,800 Tape & Reel
SBRD8360RLG−VF01*		1,800 Tape & Reel
SBRD8360T4G*		2,500 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NRVBD and SBRD Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable.

4. **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.

TYPICAL CHARACTERISTICS

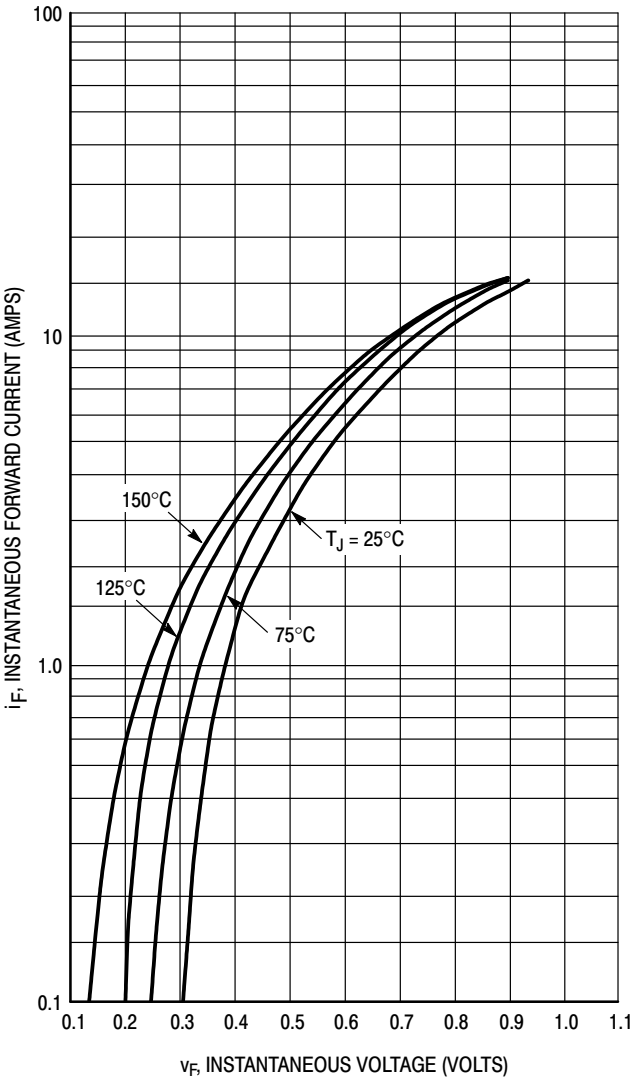
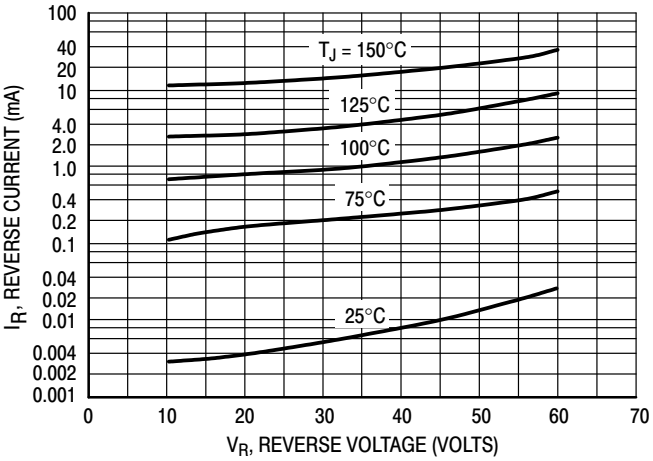


Figure 1. Typical Forward Voltage



*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these curves if V_R is sufficient below rated V_R.

Figure 2. Typical Reverse Current

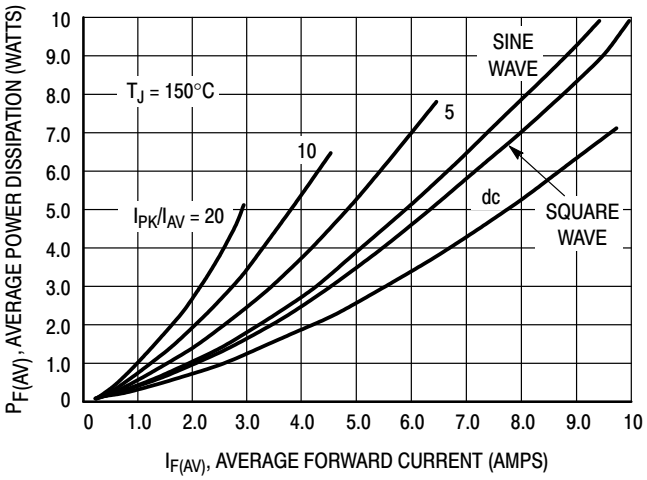


Figure 3. Average Power Dissipation

TYPICAL CHARACTERISTICS

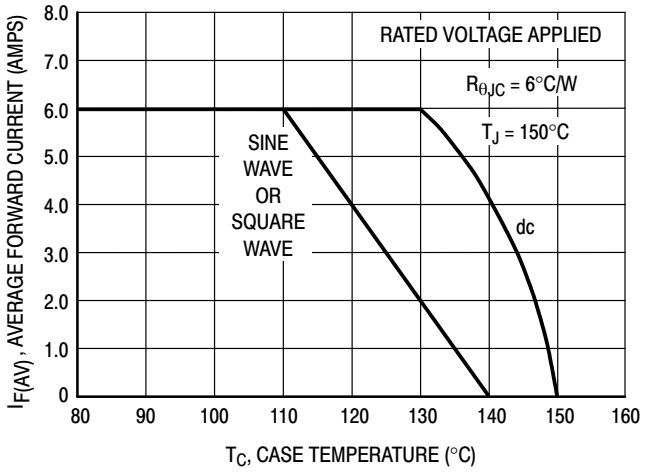


Figure 4. Current Derating, Case

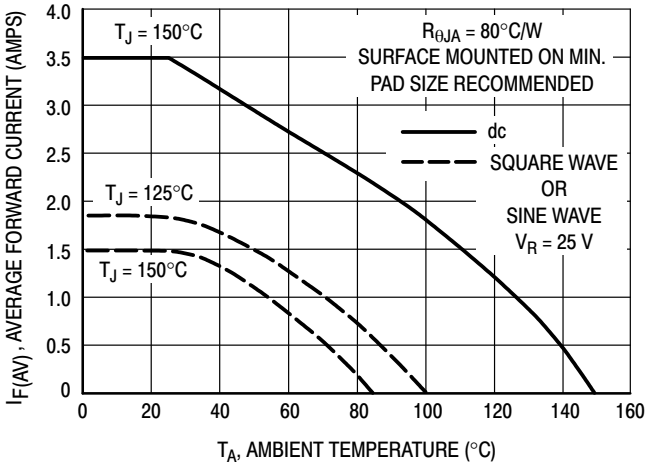


Figure 5. Current Derating, Ambient

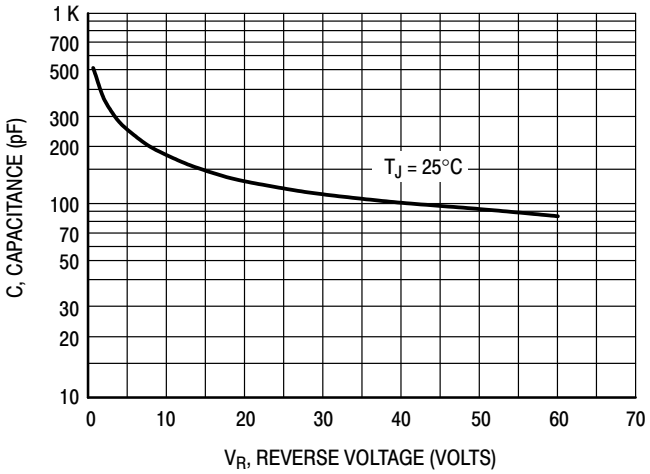
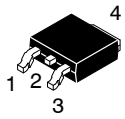


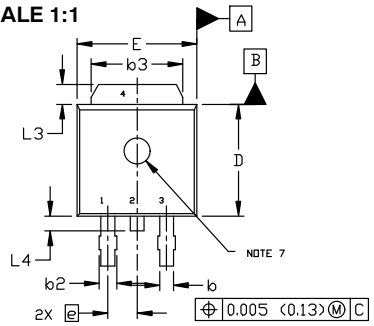
Figure 6. Typical Capacitance



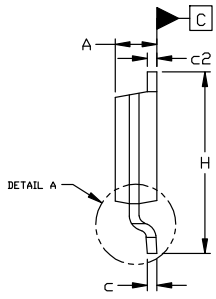
DPAK (SINGLE GAUGE)
CASE 369C
ISSUE G

DATE 31 MAY 2023

SCALE 1:1



TOP VIEW

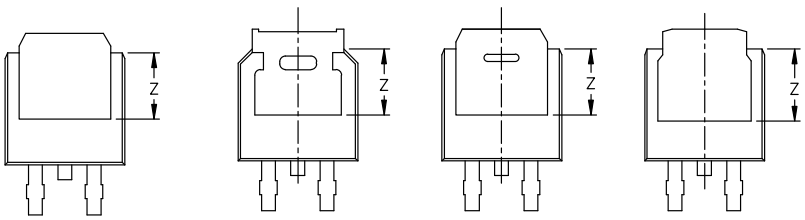


SIDE VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

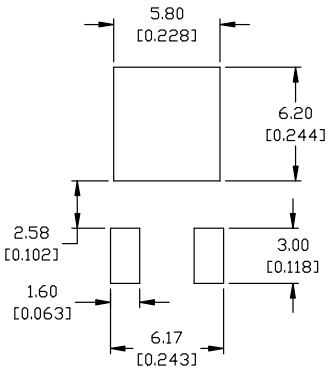
DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	----	0.040	---	1.01
Z	0.155	----	3.93	---



BOTTOM VIEW

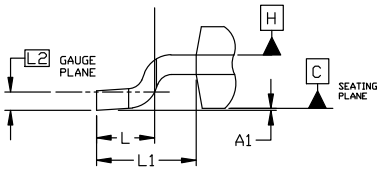
BOTTOM VIEW

ALTERNATE CONSTRUCTIONS



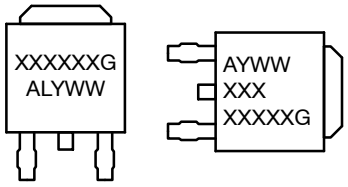
RECOMMENDED MOUNTING FOOTPRINT*

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.



DETAIL A
ROTATED 90° CW

GENERIC MARKING DIAGRAM*



IC **Discrete**

XXXXXX = Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2

STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 8:
PIN 1. N/C
2. CATHODE
3. ANODE
4. CATHODE

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. RESISTOR ADJUST
4. CATHODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

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DESCRIPTION:	**DPAK (SINGLE GAUGE)**	**PAGE 1 OF 1**

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